

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1-55. (Canceled)

56. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a first insulating film over a first substrate;

forming at least first and second thin film transistors over the first insulating film;

forming a second insulating film over the first and second thin film transistors;

forming a wiring and a first electrode over the second insulating film, wherein the wiring is connected to the first thin film transistor through a first contact hole in the second insulating film, and the first electrode is connected to the second thin film transistor through a second contact hole in the second insulating film;

forming a third insulating film over the second insulating film, the wiring, and the first electrode;

forming a third contact hole for reaching the first electrode in the third insulating film;

bonding a second substrate to a surface of the third insulating film; removing the first substrate;

forming a fourth contact hole for reaching the first thin film transistor in the first insulating film;

forming a second electrode on the first insulating film, wherein the second electrode is connected to the first thin film transistor through the fourth contact hole;

forming a fourth insulating film over the first insulating film and the second electrode; and

forming a fifth contact hole for reaching the second electrode in the fourth insulating film; and

removing the second substrate.

57. (Previously Presented) A method according to claim 56, wherein the semiconductor device is incorporated into an electronic device selected from the group consisting: a cell phone, a video camera, a mobile computer, a goggle type display, a rear projector, and a front projector.

58. (Previously Presented) A method according to claim 56, wherein the semiconductor device is an active matrix liquid crystal display device.

59. (Previously Presented) A method according to claim 56, wherein the semiconductor device is an EL display device.

60. (Previously Presented) A method according to claim 56, wherein in the step of bonding the second substrate to the surface of the third insulating film, the bonding is established by one or more bonding portions of a bonding layer.

61. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming first and second thin film devices, the method of forming the first and second thin film devices, each comprising:

forming a first insulating film over a first substrate;

forming at least first and second thin film transistors over the first insulating film;

forming a second insulating film over the first and second thin film transistors;

forming a wiring and a first electrode over the second insulating film, wherein the wiring is connected to the first thin film transistor through a first contact hole in the second insulating film, and the first electrode is connected to the second thin film transistor through a second contact hole in the second insulating film;

forming a third insulating film over the second insulating film, the wiring, and the first

electrode;

forming a third contact hole for reaching the first electrode in the third insulating film;

bonding a second substrate to a surface of the third insulating film;

removing the first substrate;

forming a fourth contact hole for reaching the first thin film transistor in the first insulating film;

forming a second electrode on the first insulating film, wherein the second electrode is connected to the first thin film transistor through the fourth contact hole;

forming a fourth insulating film over the first insulating film and the second electrode; and

forming a fifth contact hole for reaching the second electrode in the fourth insulating film; and

removing the second substrate;

bonding the first thin film device to the second thin film device so that the fifth contact hole of the first thin film device is opposed to the third contact hole of the second thin film device,

wherein a conductive connection is made in the third and fifth contact holes opposed to each other.

62. (Previously Presented) A method according to claim 61, wherein the semiconductor device is incorporated into an electronic device selected from the group consisting: a cell phone, a video camera, a mobile computer, a goggle type display, a rear projector, and a front projector.

63. (Previously Presented) A method according to claim 61, wherein the semiconductor device is an active matrix liquid crystal display device.

64. (Previously Presented) A method according to claim 61, wherein the semiconductor device is an EL display device.

65. (Previously Presented) A method according to claim 61, wherein in the step of bonding the second substrate to the surface of the third insulating film, the bonding is established by one or more bonding portions of a bonding layer.

66. (Previously Presented) A method according to claim 61, wherein a conductive paste is formed in the third and fifth contact holes.

67. (Previously Presented) A method of manufacturing a semiconductor device comprising:

forming first, second, and third thin film devices, the method of forming the first, second, and third thin film devices, each comprising:

forming a first insulating film over a first substrate;

forming at least first and second thin film transistors over the first insulating film;

forming a second insulating film over the first and second thin film transistors;

forming a wiring and a first electrode over the second insulating film, wherein the wiring is connected to the first thin film transistor through a first contact hole in the second insulating film, and the first electrode is connected to the second thin film transistor through a second contact hole in the second insulating film;

forming a third insulating film over the second insulating film, the wiring, and the first electrode;

forming a third contact hole for reaching the first electrode in the third insulating film;

bonding a second substrate to a surface of the third insulating film;

removing the first substrate;

forming a fourth contact hole for reaching the first thin film transistor in the first insulating film;

forming a second electrode on the first insulating film, wherein the second electrode is connected to the first thin film transistor through the fourth contact hole;

forming a fourth insulating film over the first insulating film and the second electrode;  
and

forming a fifth contact hole for reaching the second electrode in the fourth insulating  
film; and

removing the second substrate;

bonding the first thin film device to the second thin film device so that the fifth contact  
hole of the first thin film device is opposed to the third contact hole of the second thin film  
device, and bonding the third thin film device to the second thin film device so that the third  
contact hole of the third thin film device is opposed to the fifth contact hole of the second thin  
film device,

wherein a conductive connection is made in the third and fifth contact holes opposed to  
each other.

68. (Previously Presented) A method according to claim 67, wherein the semiconductor  
device is incorporated into an electronic device selected from the group consisting: a cell phone,  
a video camera, a mobile computer, a goggle type display, a rear projector, and a front projector.

69. (Previously Presented) A method according to claim 67, wherein the semiconductor  
device is an active matrix liquid crystal display device.

70. (Previously Presented) A method according to claim 67, wherein the semiconductor  
device is an EL display device.

71. (Previously Presented) A method according to claim 67, wherein in the step of  
bonding the second substrate to the surface of the third insulating film, the bonding is established  
by one or more bonding portions of a bonding layer.

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72. (Previously Presented) A method according to claim 67, wherein a conductive paste is formed in the third and fifth contact holes.

73-92. (Canceled)